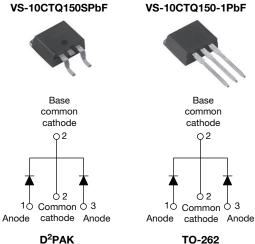


Vishay Semiconductors

High Performance Schottky Rectifier, 2 x 5 A



TO-262

PRODUCT SUMMARY					
Package	D ² PAK, TO-262				
I _{F(AV)}	2 x 5 A				
V _R	150 V				
V _F at I _F	0.93 V				
I _{RM}	7 mA at 125 °C				
T _J max.	175 °C				
Diode variation	Common cathode				
E _{AS}	5 mJ				

FEATURES

- 175 °C T_J operation
- · Center tap configuration
- · Low forward voltage drop
- High frequency operation
- RoHS • High purity, high temperature epoxy COMPLIANT HALOGEN encapsulation for enhanced mechanical FREE strength and moisture resistance
- · Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

This center tap Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Rectangular waveform	10	А			
V _{RRM}		150	V			
I _{FSM}	t _p = 5 μs sine	620	A			
V _F	5 A_{pk} , T_J = 125 °C (per leg)	0.73	V			
TJ	Range	-55 to +175	°C			

VOLTAGE RATINGS			
PARAMETER	SYMBOL	VS-10CTQ150SPbF VS-10CTQ150-1PbF	UNITS
Maximum DC reverse voltage	V _R	150	V
Maximum working peak reverse voltage	V _{RWM}	150	V

ABSOLUTE MAXIMUM RATI	NGS				
PARAMETER	SYMBOL	TEST COND	ITIONS	VALUES	UNITS
Maximum average per leg	I	50 % duty cycle at $T_{\rm C}$ = 155 °C	raatangular wayafarm	5	Δ
forward current, see fig. 5 per device	I _{F(AV)}	50% duty cycle at $T_C = 155\%$ C	, rectangular wavelonn	10	A
Maximum peak one cycle non-repetitive	_	5 µs sine or 3 µs rect. pulse	Following any rated load	620	
surge current per leg, see fig. 7	I _{FSM}	10 ms sine or 6 ms rect. pulse	condition and with rated V _{RRM} applied	115	A
Non-repetitive avalanche energy per leg	E _{AS}	T _J = 25 °C, I _{AS} = 1 A, L = 10 mH	ł	5	mJ
Repetitive avalanche current per leg	I _{AR}	Current decaying linearly to zero Frequency limited by T _J maximu		1	А

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ELECTRICAL SE	PECIFICATIONS
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PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
		5 A	T.I = 25 °C	0.93	
Maximum forward voltage drop per leg	V _{FM} ⁽¹⁾	10 A	1j=25 C	1.10	V
See fig. 1	VFM (*)	5 A	T.I = 125 °C	0.73	.10 V .73 V .86 mA .05 mA 468 V 28 mΩ
		10 A	$-1_{\rm J} = 125$ C	0.86	
Maximum reverse leakage current per leg	1 (1)	T _J = 25 °C		0.05	
See fig. 2	IRM (')	T _J = 125 °C	$V_R = Rated V_R$	7	mA
Threshold voltage	V _{F(TO)}	T T maximum		0.468	V
Forward slope resistance	r _t	$T_J = T_J$ maximum		28	mΩ
Maximum junction capacitance per leg	CT	$V_R = 5 V_{DC}$ (test signal ran	ge 100 kHz to 1 MHz), 25 °C	200	pF
Typical series inductance per leg	L _S	Measured lead to lead 5 m	nm from package body	8.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 %

THERMAL - MECH	ANICAL SP	ECIFICAT	IONS		
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and stor temperature range	Maximum junction and storage temperature range			-55 to +175	°C
Maximum thermal resistance junction to case per leg	ce,	P	DC operation	3.50	
Maximum thermal resistance junction to case per package	,	– R _{thJC}		1.75 °C/W	
Typical thermal resistance, case to heatsink (only for T	O-220)	R _{thCS}	ounting surface, smooth and greased 0.50		
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking davice			Case style D ² PAK	10CTQ1	50S
Marking device			Case style TO-262	10CTQ1	50-1



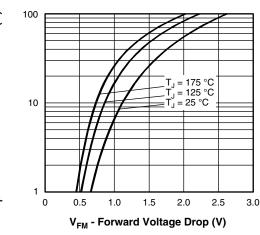
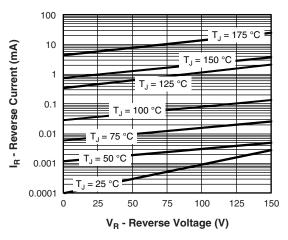
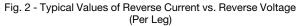


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)





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VS-10CTQ150SPbF, VS-10CTQ150-1PbF

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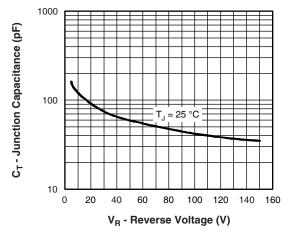


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

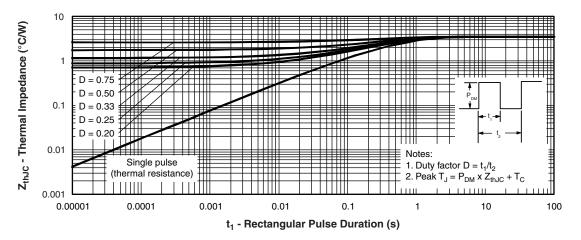


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

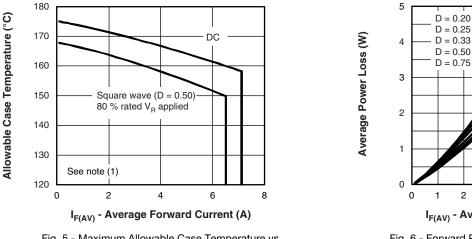


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

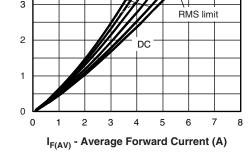


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

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VS-10CTQ150SPbF, VS-10CTQ150-1PbF

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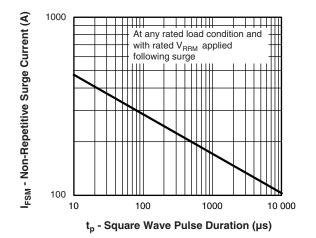


Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

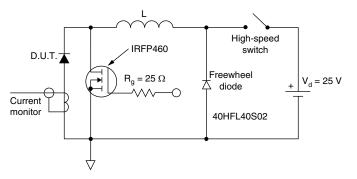


Fig. 8 - Unclamped Inductive Test Circuit

Note

 $^{(1)}$ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC};$ Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D); I_R$ at $V_{R1} = 10 \text{ V}$

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VS-10CTQ150SPbF, VS-10CTQ150-1PbF

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ORDERING INFORMATION TABLE

Device code	vs-	10	С	т	Q	150	S	TRL	PbF
		2	3	4	5	6	7	8	9
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	Cur Circ T = Sch	rent rati cuit conf TO-220 nottky "C)" series ng (150	n: C = c	ommon	cathod	e	
	8 -	• N • TI • TI	RL = tap RR = taj	62 be (50 p be and re be and r (Pb)-fre	eel (left eel (righ				

LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95014
Part marking information	www.vishay.com/doc?95008
Packaging information	www.vishay.com/doc?95032

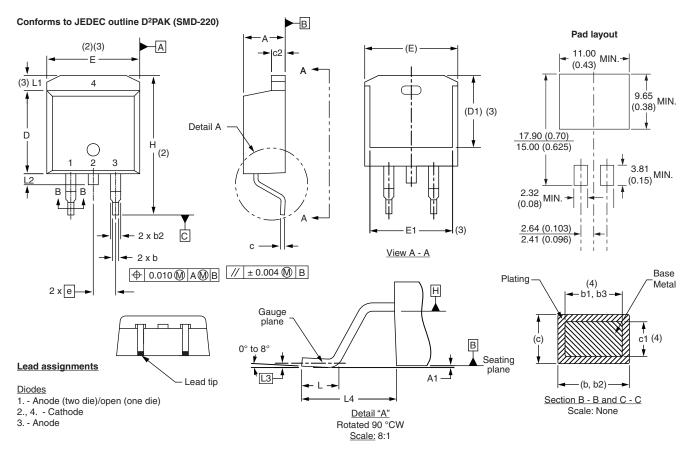


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Vishay Semiconductors

D²PAK, TO-262



DIMENSIONS - D²PAK in millimeters and inches

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SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
с	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

INCHES

MILLIMETERS

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- ⁽⁴⁾ Dimension b1 and c1 apply to base metal only
- ⁽⁵⁾ Datum A and B to be determined at datum plane H
- ⁽⁶⁾ Controlling dimension: inch

Document Number: 95014 Revision: 31-Mar-09

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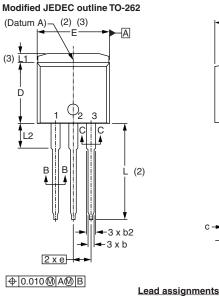
Outline Dimensions

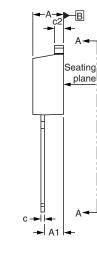
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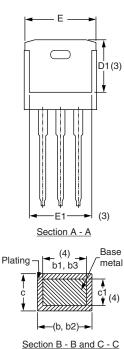
D²PAK, TO-262



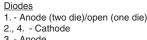
DIMENSIONS - TO-262 in millimeters and inches

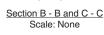






Lead tip





SYMBOL	MILLIN	METERS	INCI	NOTEO	
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100	BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Controlling dimension: inches

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actual package outline

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the

3. - Anode



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